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Docket No.: M4065.0959/P959
(PATENT)

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of:
Dean A. Klein

Application No.: 10/796,111 | Confirmation No.: 2460

Filed: March 10, 2004 | Art Unit: 2818

For: POWER MANAGEMENT CONTROL AND CONTROLLING MEMORY REFRESH OPERATIONS | Examiner: Not Yet Assigned

## INFORMATION DISCLOSURE STATEMENT (IDS)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 CFR 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is filed within three months of the U.S. filing date (37 CFR 1.97(b)(1)).

Pursuant to United States Patent and Trademark Office Official Gazette Notice: 05 August 2003 ("Information Disclosure Statements May Be Filed Without Copies of U.S. Patents and Published Applications in Patent Applications filed after June 30, 2003") copies of the U.S. Patent Document references (i.e., references AA-AU7 ) on the PTO/SB/08 are not provided. Copies of the Foreign Patent Document references (i.e.,

references BA, BB, and BC) and the Other Prior Art – Non Patent Literature Document References (i.e., references CA – CO6) on the PTO/SB/08 are provided.

In accordance with 37 CFR 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 CFR 1.56(a) exists. In accordance with 37 CFR 1.97(h), the filing of this Information Disclosure statement shall not be construed to be an admission that any patent, publication or other information referred to therein is "prior art" for this invention unless specifically designated as such.

It is submitted that the Information Disclosure Statement is in compliance with 37 CFR 1.98 and the Examiner is respectfully requested to consider the listed references.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0959/P959. A duplicate copy of this paper is enclosed.

Dated: June 10, 2004

Respectfully submitted,

By _____

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# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

*(use as many sheets as necessary)*

| Sheet | 1 | of | 13 |
|---|---|---|---|

| *Complete if Known* | |
|---|---|
| **Application Number** | 10/796,111 |
| **Filing Date** | March 10, 2004 |
| **First Named Inventor** | Dean A. Klein |
| Art Unit | 2818 |
| Examiner Name | Not Yet Assigned |
| Attorney Docket Number | M4065.0959/P0959 |

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Sheet 2 of 13

| *Complete if Known* | |
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| Application Number | 10/796,111 |
| Filing Date | March 10, 2004 |
| First Named Inventor | Dean A. Klein |
| Art Unit | 2818 |
| Examiner Name | Not Yet Assigned |
| Attorney Docket Number | M4065.0959/P0959 |

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# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 3 of 13

| *Complete if Known* | |
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| Application Number | 10/796,111 |
| Filing Date | March 10, 2004 |
| First Named Inventor | Dean A. Klein |
| Art Unit | 2818 |
| Examiner Name | Not Yet Assigned |
| Attorney Docket Number | M4065.0959/P0959 |

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# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

*(use as many sheets as necessary)*

Sheet 4 of 13

| *Complete if Known* | |
|---|---|
| Application Number | 10/796,111 |
| Filing Date | March 10, 2004 |
| First Named Inventor | Dean A. Klein |
| Art Unit | 2818 |
| Examiner Name | Not Yet Assigned |
| Attorney Docket Number | M4065.0959/P0959 |

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Sheet 5 of 13

| *Complete if Known* | |
|---|---|
| **Application Number** | 10/796,111 |
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| **First Named Inventor** | Dean A. Klein |
| Art Unit | 2818 |
| Examiner Name | Not Yet Assigned |
| Attorney Docket Number | M4065.0959/P0959 |

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| Examiner Signature | | Date Considered | |
|---|---|---|---|

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

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# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 6 of 13

| *Complete if Known* | |
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| Application Number | 10/618,824 |
| Filing Date | July 14, 2003 |
| First Named Inventor | Terry L. Gilton |
| Group Art Unit | N/A |
| Examiner Name | Not Yet Assigned |
| Attorney Docket Number | M4065.1006/P1006-A |

**OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS**

| Examiner Initials* | Cite No.[1] | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published. | T[2] |
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|---|---|
| Application Number | 10/618,824 |
| Filing Date | July 14, 2003 |
| First Named Inventor | Terry L. Gilton |
| Group Art Unit | N/A |
| Examiner Name | Not Yet Assigned |
| Attorney Docket Number | M4065.1006/P1006-A |

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